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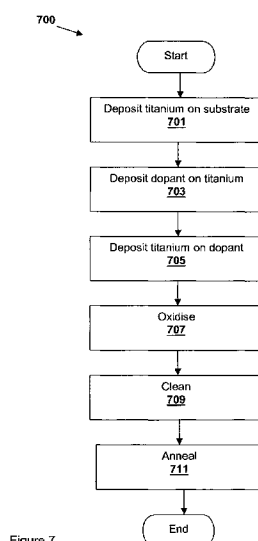
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(54) Title: METHOD FOR IN-SITU DOPING OF TITANIUM DIOXIDE FILM



(57) Abstract: A method of producing a titanium dioxide film with dopant uniformly dispersed throughout the entirety of the film. The method involves deposition of dopant, concurrently or sequentially, with titanium before oxidation of the titanium. No separate doping step is required in this invention since the doping step occurs in-situ during oxidation process. The amount of dopant incorporated into a titanium dioxide film is controllable by varying the thickness and/or number of dopant layers deposited. Furthermore, dispersion of dopant throughout the titanium dioxide film is more uniform in this invention as multiple layers of dopant may be employed.